

RECTRON
SEMICONDUCTOR
TECHNICAL SPECIFICATION

DB1012S

**SINGLE-PHASE GLASS PASSIVATED
SILICON BRIDGE RECTIFIER**

VOLTAGE 1200 Volts CURRENT 1.0 Ampere

FEATURES

- * Surge overload rating - 50 amperes peak
- * Ideal for printed circuit board
- * Reliable low cost construction utilizing molded
- * Glass passivated device
- * Polarity symbols molded on body
- * Mounting position: Any
- * Weight: 1.0 gram

MECHANICAL DATA:

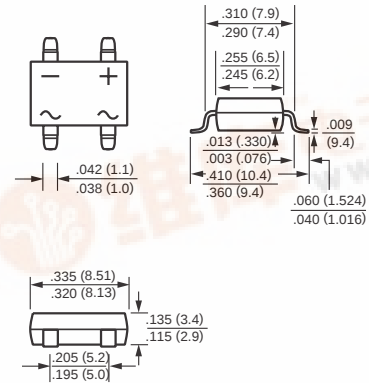
- * Epoxy : UL flammability classification 94V-0

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified.
Single phase, half wave, 60 Hz, resistive or inductive load.
For capacitive load, derate current by 20%.



DB-S



Dimensions in inches and (millimeters)

MAXIMUM RATINGS (At TA = 25°C unless otherwise noted)

RATINGS	SYMBOL	DB1012S	UNITS
Maximum Recurrent Peak Reverse Voltage	VRRM	1200	Volts
Maximum RMS Bridge Input Voltage	VRRMS	840	Volts
Maximum DC Blocking Voltage	VDC	1200	Volts
Maximum Average Forward Output Current at TA = 40°C	IO	1.0	Amps
Peak Forward Surge Current 8.3 ms single half sine-wave superimposed on rated load (JEDEC method)	IFSM	50	Amps
Operating and Storage Temperature Range	TJ, TSTG	-55 to + 150	°C

ELECTRICAL CHARACTERISTICS (At TA = 25°C unless otherwise noted)

CHARACTERISTICS	SYMBOL	DB1012S	UNITS
Maximum Forward Voltage Drop per Bridge Element at 1.0A DC	VF	1.1	Volts
Maximum Reverse Current at rated DC Blocking Voltage per element	IR	5.0	uAmps
		0.5	mAmps

NOTE: Suffix "S" Surface Mount for Dip Bridge.

RATING AND CHARACTERISTIC CURVES OF DB1012S

FIG. 1 - MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

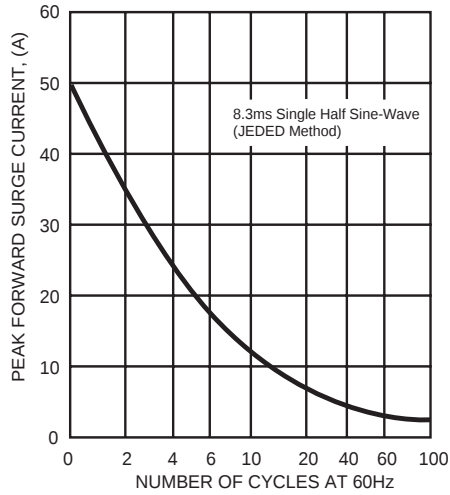


FIG. 2 - TYPICAL FORWARD CURRENT DERATING CURVE

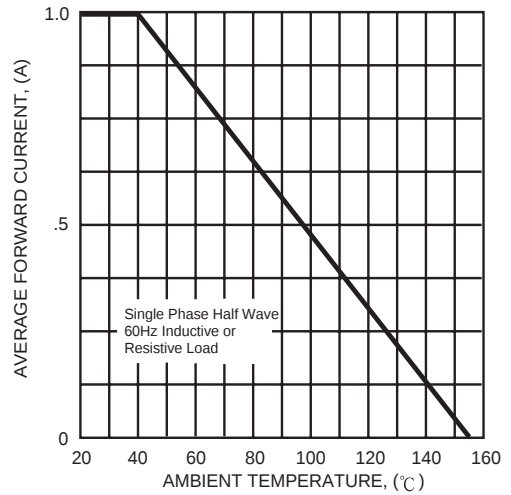


FIG. 3 - TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

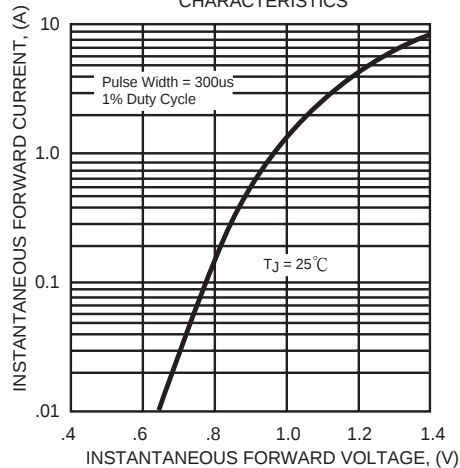


FIG. 4 - TYPICAL REVERSE CHARACTERISTICS

